





50V NPN SILICON LOW SATURATION TRANSISTOR IN SOT23

Features

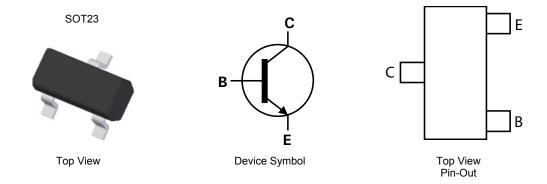
- BV_{CEO} > 50V
- I_C = 2A Continuous Collector Current
- 625mW power dissipation
- Low Saturation Voltage V_{CE(sat)} < 200mV @ 1A
- $R_{CE(SAT)} = 68m\Omega$ for a low equivalent on-resistance
- h_{FE} characterised up to 6A for high current gain hold-up
- Complementary PNP type: FMMT720
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP capable (Note 4)

Mechanical Data

- Case: SOT23
- Case Material: molded plastic, "Green" molding compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight 0.008 grams (approximate)

Applications

- MOSFET Gate Driving
- DC-DC / DC-AC Converters
- Regulator
- LED driver
- Motor Control



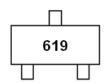
Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FMMT619TA	AEC-Q101	619	7	8	3,000
FMMT619QTA	Automotive	619	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified.
- 5. For packaging details, go to our website at http://www.diodes.com

Marking Information



619 = Product Type Marking Code





Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	50	V
Collector-Emitter Voltage	V _{CEO}	50	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	Ic	2	Α
Peak Pulse Current	I _{CM}	6	Α
Base Current	I _B	500	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

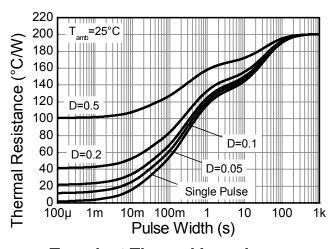
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P _D	625	mW
Power Dissipation (Note 7)	P _D	806	mW
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	200	°C/W
Thermal Resistance, Junction to Ambient (Note 7)	$R_{\theta JA}$	155	°C/W
Thermal Resistance, Junction to Leads (Note 8)	R ₀ JL	194	°C/W
Operating and Storage Temperature Range	$T_{J_i} T_{STG}$	-55 to +150	°C

Notes:

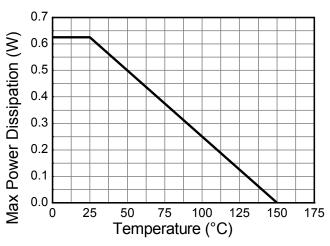
^{6.} For a device surface mounted on 25mm X 25mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
7. Same as note 6, except the device is measured at t ≤ 5 sec.
8. Thermal resistance from junction to solder-point (at the end of the collector lead).



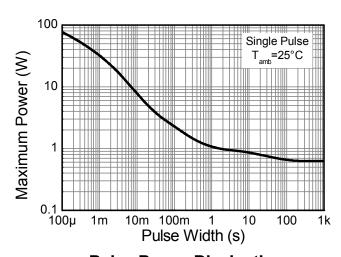
Thermal Characteristics and Derating information



Transient Thermal Impedance



Derating Curve



Pulse Power Dissipation





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

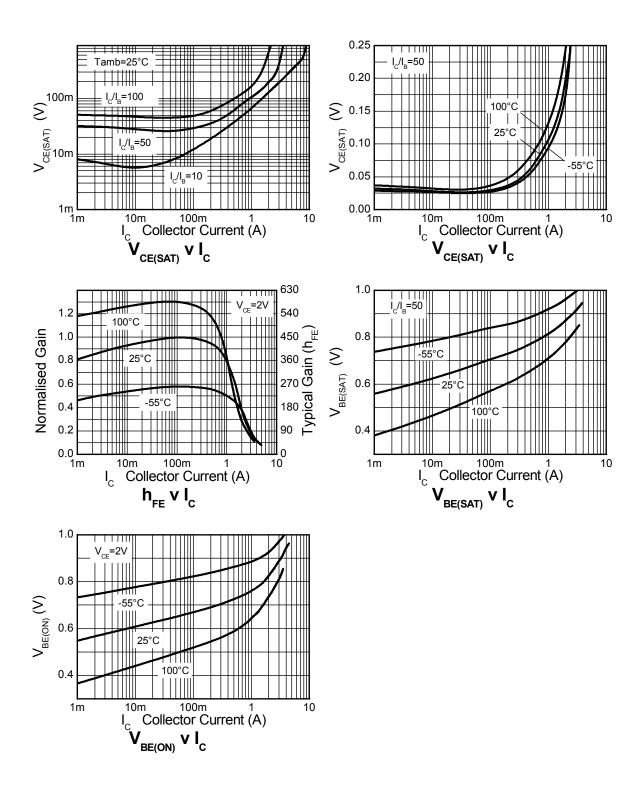
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	50	190	-	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	50	65	-	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.3	-	V	I _E = 100μA
Collector Cut-off Current	I _{CBO}	-	-	100	nA	V _{CB} = 40V
Emitter Cut-off Current	I _{EBO}	-	-	100	nA	V _{EB} = 6V
Collector Emitter Cut-off Current	I _{CES}	-	-	100	nA	V _{CES} = 40V
ON CHARACTERISTICS (Note 9)						
Static Forward Current Transfer Ratio	h _{FE}	200 300 200 100	400 450 400 225 40	- - -	-	$\begin{split} & I_{C} = 10 \text{mA}, \ V_{CE} = 2 \text{V} \\ & I_{C} = 200 \text{mA}, \ V_{CE} = 2 \text{V} \\ & I_{C} = 1 \text{A}, \ V_{CE} = 2 \text{V} \\ & I_{C} = 2 \text{A}, \ V_{CE} = 2 \text{V} \\ & I_{C} = 6 \text{A}, \ V_{CE} = 2 \text{V} \end{split}$
Collector-Emitter Saturation Voltage	V _{CE(sat)}	- - -	10 125 150	20 200 220	mV	$I_C = 0.1A$, $I_B = 10mA$ $I_C = 1A$, $I_B = 10mA$ $I_C = 2A$, $I_B = 50mA$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	-	0.87	1.0	V	$I_C = 2A$, $I_B = 50mA$
Base-Emitter Saturation Voltage	$V_{BE(on)}$	-	0.82	1.0	V	I _C = 2A, V _{CE} = 2V
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f_T	100	165	-	MHz	I _C = 50mA, V _{CE} = 10V, f = 100MHz
Collector Output Capacitance	C_{obo}	-	12	20	pF	V _{CB} = 10V, f = 1MHz
Turn-On Time	t _(on)	-	170	-	ns	V _{CC} = 10V, I _C = 1A,
Turn-Off Time	$t_{(off)}$	-	750	-	ns	$I_{B1} = -I_{B2} = 10 \text{mA}$

Notes: 9. Measured under pulsed conditions. Pulse width $\leq 300\mu s$. Duty cycle $\leq 2\%$





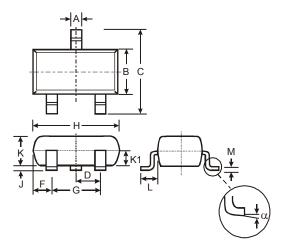
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)





Package Outline Dimensions

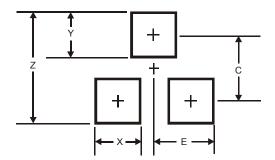
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
7	0.013	0.10	0.05		
K	0.903	1.10	1.00		
K1	-	-	0.400		
L	0.45	0.61	0.55		
М	0.085	0.18	0.11		
α	0°	8°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
С	2.0
ш	1.35





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